

# OPERATION OF MOSFET

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# Derivation of I-V characteristic

## ► Channel Charge Density

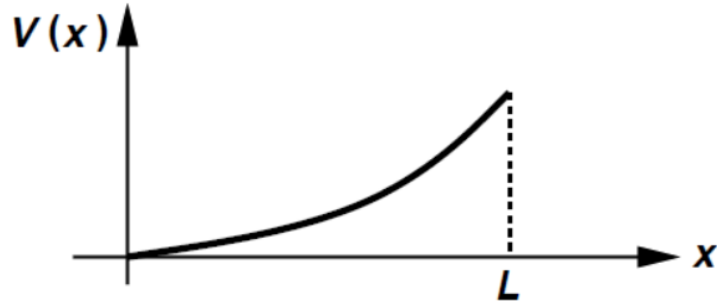
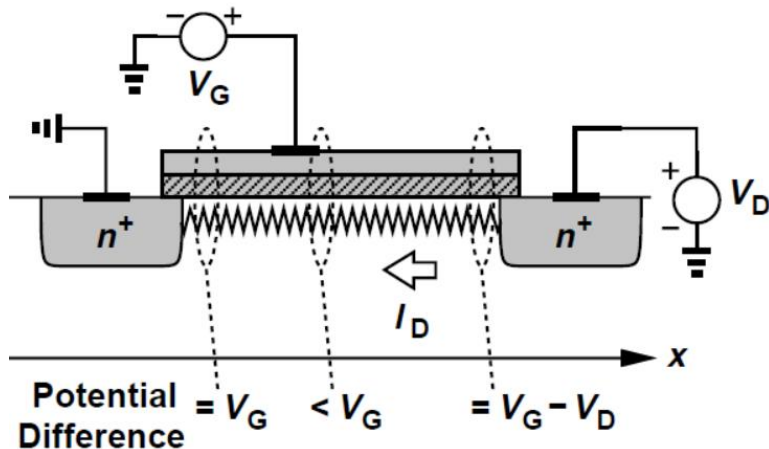
case1.  $V_{GS} > V_{TH}, V_D = 0$

$$Q = WC_{ox}(V_{GS} - V_{TH})$$

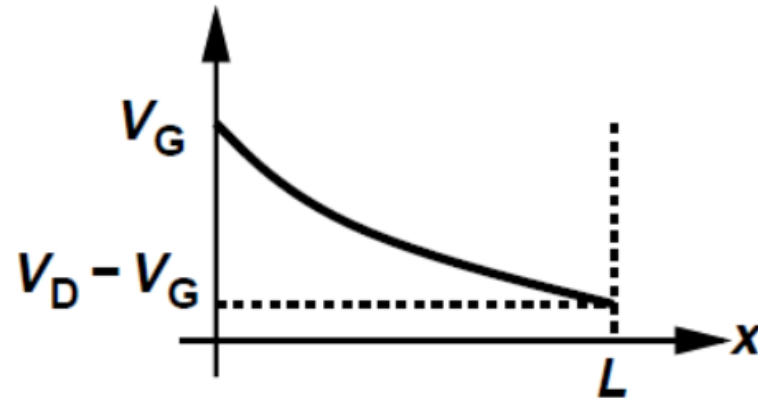
capacitance per unit area      overdrive voltage

case2.  $V_{GS} > V_{TH}, V_D > 0$

$$Q(x) = WC_{ox}[V_{GS} - \underline{V(x)} - V_{TH}]$$

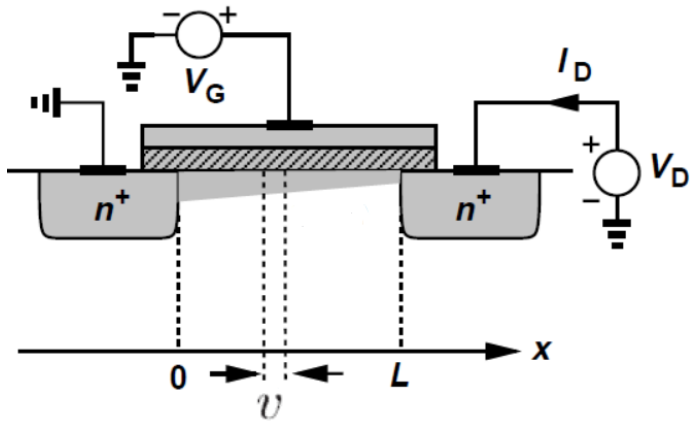


## Gate-Substrate Potential Difference



# Derivation of I-V characteristics

## ► Drain Current



$$v = -\mu_n E,$$

$$= +\mu_n \frac{dV}{dx}$$

total charge in this length

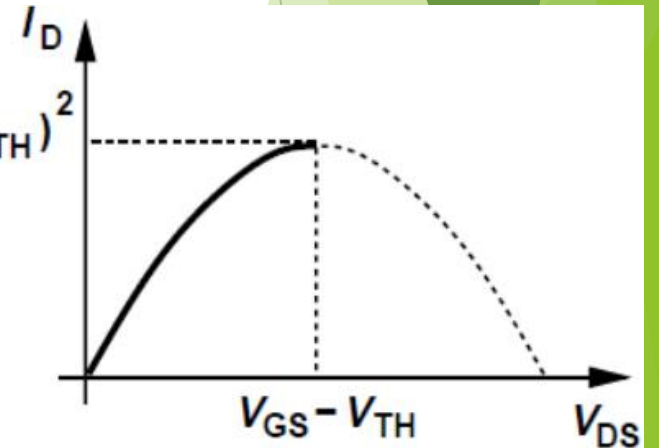
$$vw C_{OX} (V_{GS} - V_{TH} - V(x))$$

$$I_D = WC_{ox} [V_{GS} - V(x) - V_{TH}] \mu_n \frac{dV(x)}{dx}$$

$$\int_{x=0}^{x=L} I_D dx = \int_{V(x)=0}^{V(x)=V_{DS}} \mu_n C_{ox} W [V_{GS} - V(x) - V_{TH}] dV.$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} [2(V_{GS} - V_{TH})V_{DS} - V_{DS}^2]$$

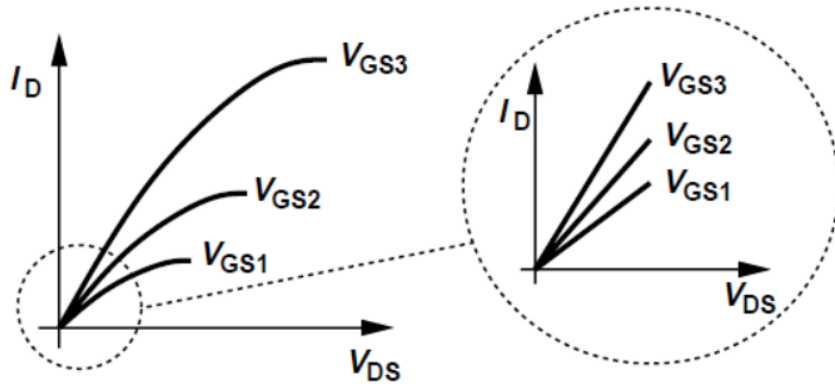
$$\frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$



# $I_D$ - $V_{DS}$ Characteristics

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} [2(V_{GS} - V_{TH})V_{DS} - V_{DS}^2]$$

- ▶ How about  $V_{DS}$  has very small value?



$$I_D \approx \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH}) V_{DS}$$

$$R_{on} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})}$$

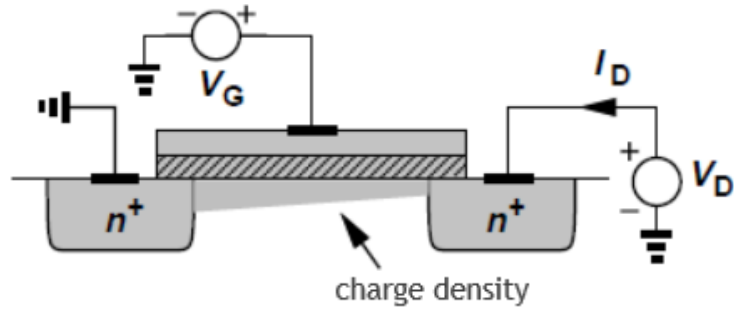
- A MOSFET can act as a voltage-dependent resistor.
- MOSFET can be a switch. (ON :  $V_{GS} \gg V_{TH}$ , OFF :  $V_{GS} = V_{TH}$ )

Only in situation that  $V_{DS} \ll 2(V_{GS} - V_{TH})!!$

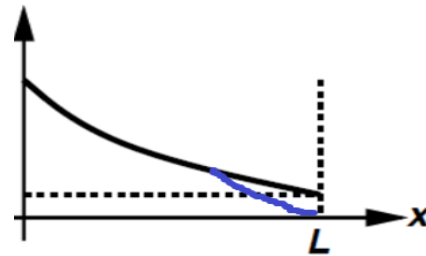
# $I_D$ - $V_{DS}$ Characteristics

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} [2(V_{GS} - V_{TH})V_{DS} - V_{DS}^2]$$

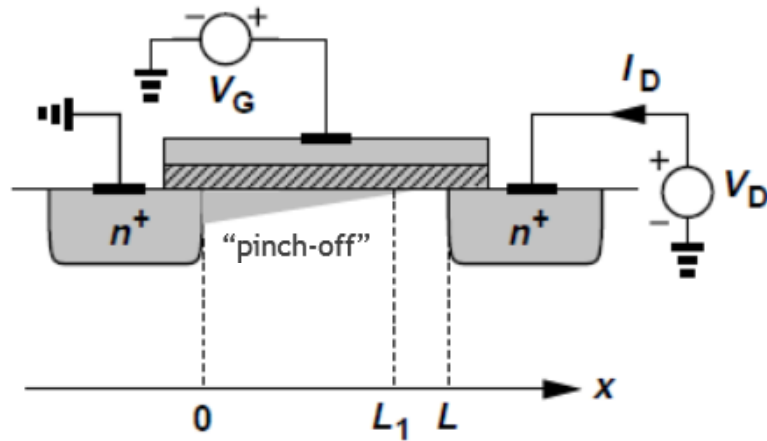
- ▶ How about  $V_{DS}$  is bigger than  $V_{GS} - V_{TH}$



if  $V_{GS} - V_{DS} = V_{TH}$ , the charge drops to zero!!



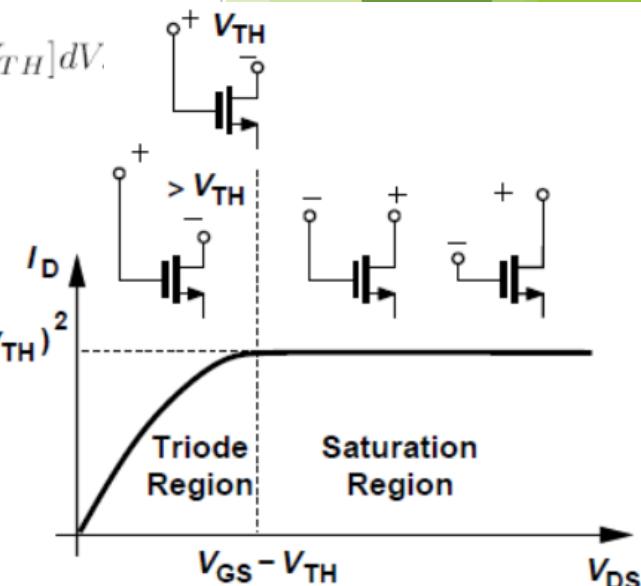
If  $V_{DS}$  is beyond  $V_{GS} - V_{TH}$ , the point that the charge density go to zero goes left.



$$\int_{x=0}^{x=L_1} I_D dx = \int_{V(x)=0}^{V(x)=V_{GS}-V_{TH}} \mu_n C_{ox} W [V_{GS} - V(x) - V_{TH}] dV$$

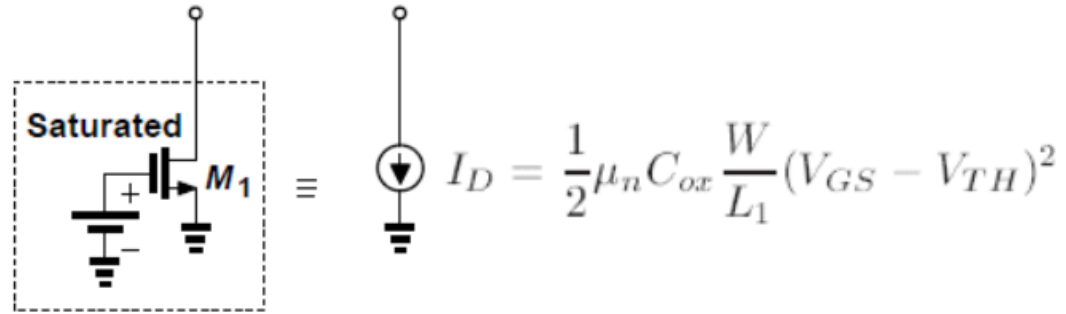
$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L_1} (V_{GS} - V_{TH})^2$$

$$\frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

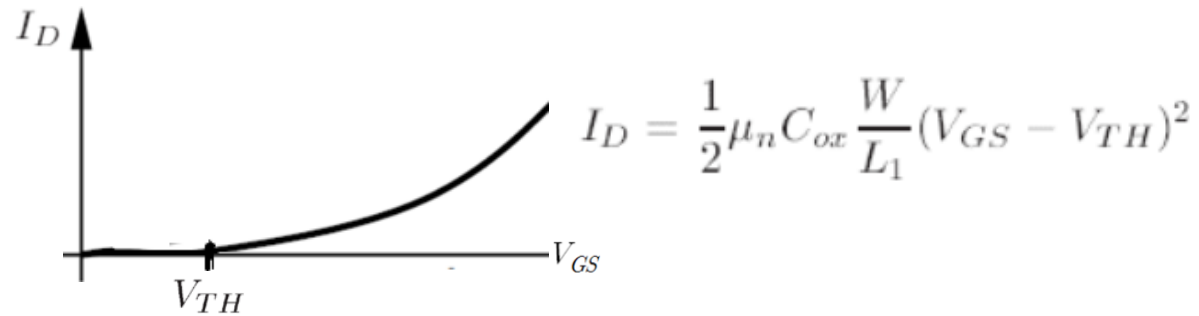


# About Saturation

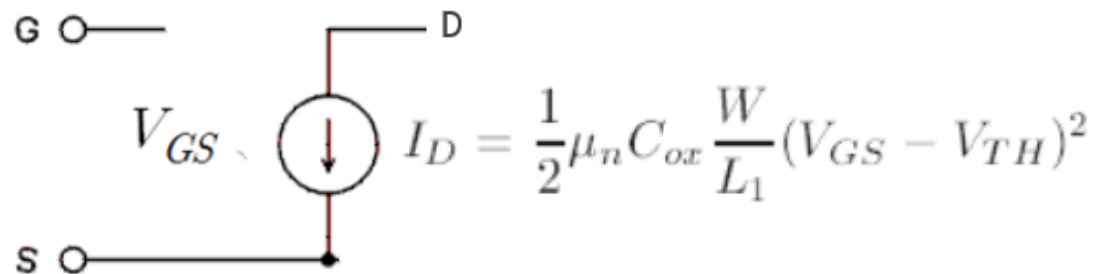
- ▶ Work as Current source



- ▶  $I_D$ - $V_{GS}$  characteristic in saturated situation



- ▶ Simple model in saturation (using this device, we can build an amplifier.)



**Thank you for your attention!!**